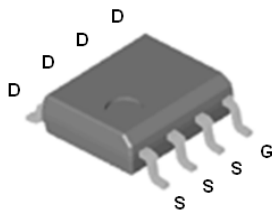


# P2003EVT

## P-Channel Enhancement Mode MOSFET

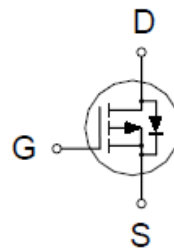
### PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
-30V	20mΩ @ $V_{GS} = -10V$	-9A



SOP- 08

100% UIS tested



### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	±25	
Continuous Drain Current	$T_C = 25\text{ °C}$	$I_D$	-9	A
	$T_C = 70\text{ °C}$		-8	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	-32	
Avalanche Current		$I_{AS}$	-28	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	40	mJ
Power Dissipation	$T_C = 25\text{ °C}$	$P_D$	2.5	W
	$T_C = 70\text{ °C}$		1.3	
Operating Junction & Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	°C

### THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta Jc}$		25	°C / W
Junction-to-Ambient	$R_{\theta JA}$		50	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle ≤ 1%

# P2003EVT

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### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.5	-3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±25V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V			-1	μA
		V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125 °C			-10	
On-State Drain Current <sup>1</sup>	I <sub>D(ON)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> = -10V	-50			A
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7A		25	35	mΩ
		V <sub>GS</sub> = -10V, I <sub>D</sub> = -9A		15	20	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -9A		24		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -15V, f = 1MHz		1610		pF
Output Capacitance	C <sub>oss</sub>			410		
Reverse Transfer Capacitance	C <sub>rss</sub>			200		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 15mV, V <sub>DS</sub> = 0V, f = 1MHz		3.4	3.7	Ω
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 0.5V <sub>(BR)DSS</sub> , I <sub>D</sub> = -9A, V <sub>GS</sub> = -10V		17	24	nC
Gate-Source Charge <sup>2</sup>	Q <sub>gs</sub>			5		
Gate-Drain Charge <sup>2</sup>	Q <sub>gd</sub>			6		
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = -15V, R <sub>L</sub> = 1Ω I <sub>D</sub> ≅ -1A, V <sub>GS</sub> = -10V, R <sub>GS</sub> = 6Ω		5.7		nS
Rise Time <sup>2</sup>	t <sub>r</sub>			10		
Turn-Off Delay Time <sup>2</sup>	t <sub>d(off)</sub>			18		
Fall Time <sup>2</sup>	t <sub>f</sub>			5		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>C</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>				-3.5	A
Pulsed Current <sup>3</sup>	I <sub>SM</sub>				-32	
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = -1A, V <sub>GS</sub> = 0V			-1.2	V

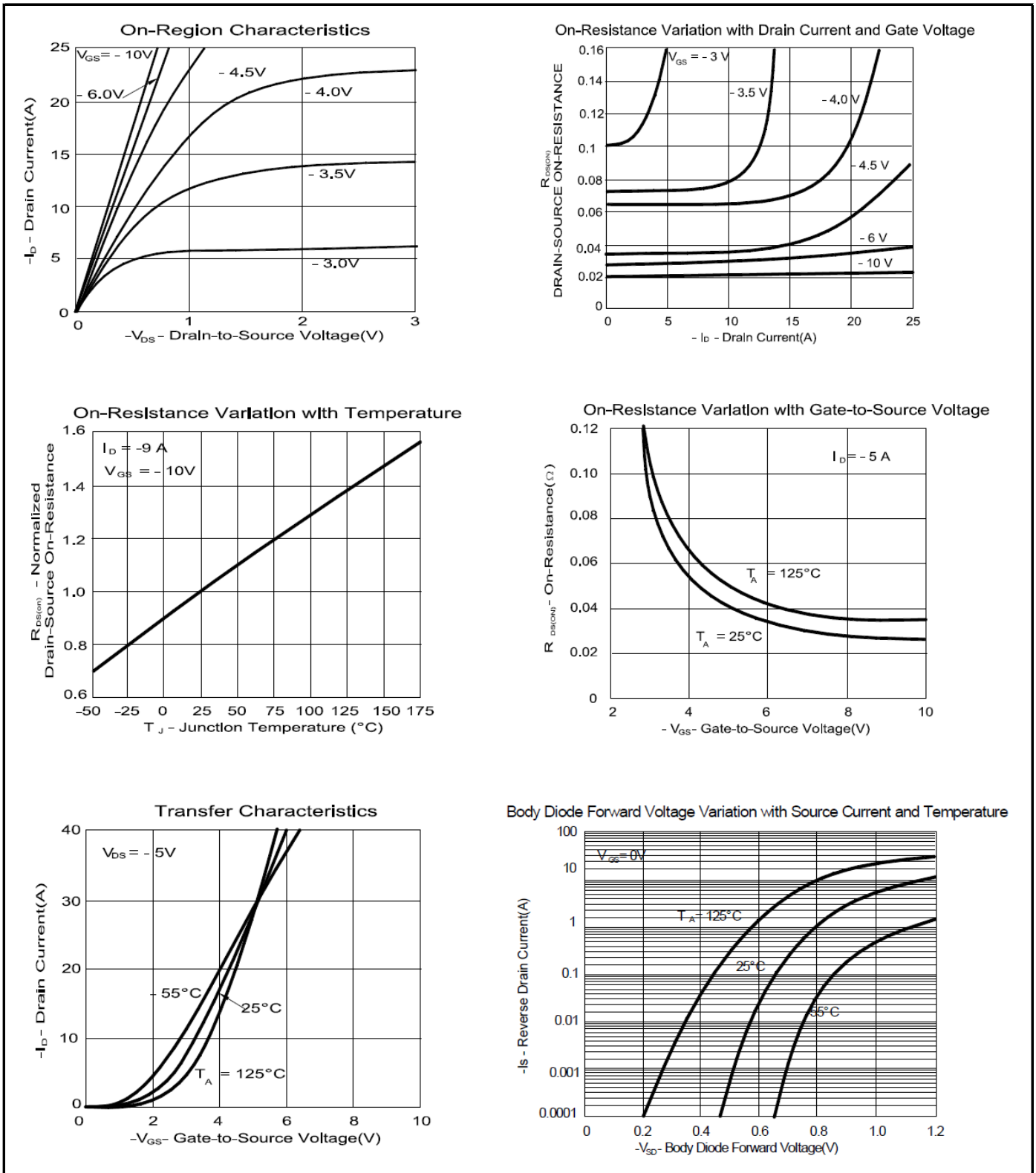
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Pulse width limited by maximum junction temperature.

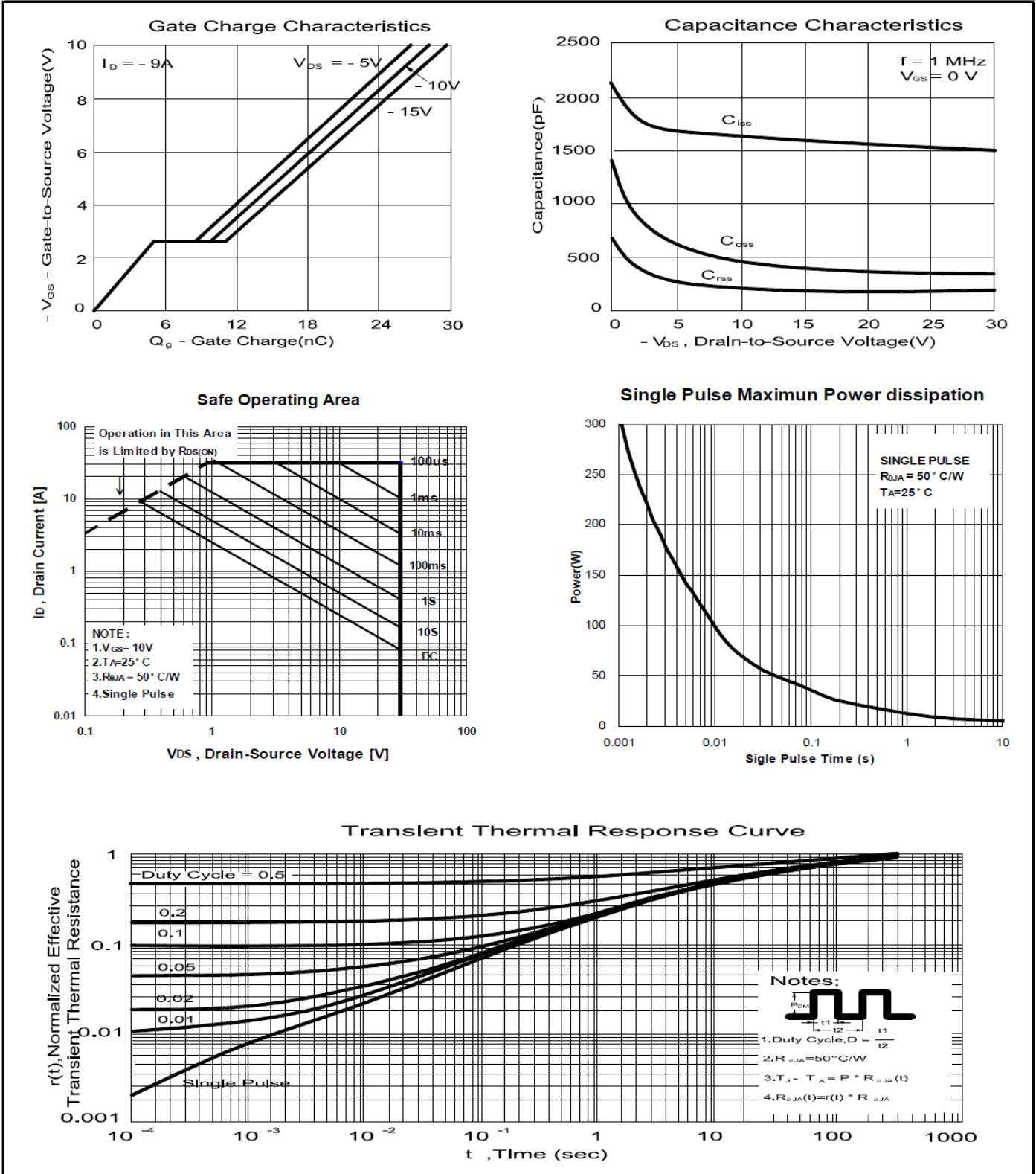
# P2003EVT

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# P2003EVT

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### Package Dimension

### SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

